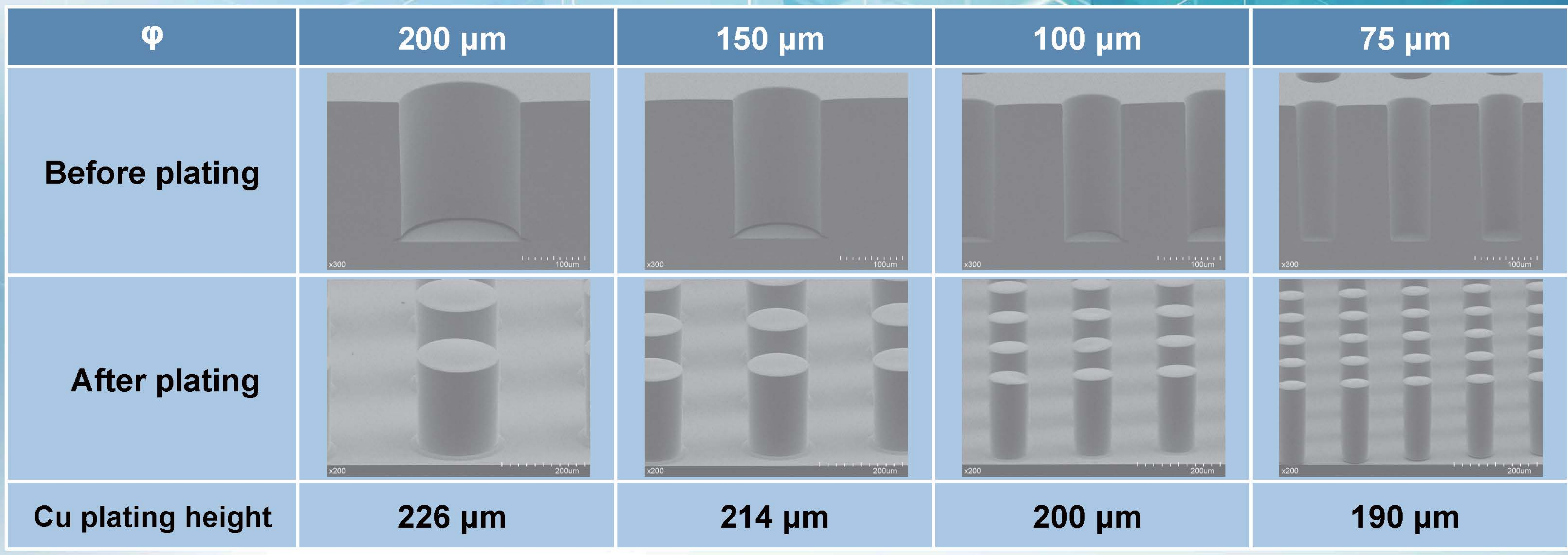
JSR ELPAC™

THB series Thick Layer Photoresist

for High Metal Pillar Bumping



φ	200 µm	150 µm	100 µm	75 µm
Before plating				
After plating				
Cu plating height	226 µm	214 µm	200 µm	190 µm

< Patterning Conditions>

Substrate: Cu sputter wafer, Soft-bake : 120 C / 5 min(1st), 120 C / 10 min(2nd), Film Thickness after Dev.: 240 µm

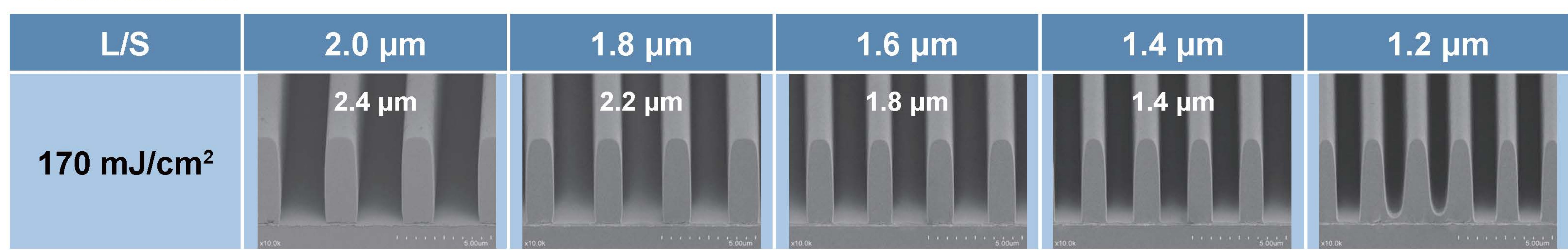
Exposure: 1000 mJ/cm^2 (ghi-line UT stepper, NA=0.16, sigma=1.00 , Focus=20 µm inside from film surface), Development : 60 sec x 6 times / 2.38 wt%TMAH

< Plating and Stripping Conditions >

Plating: Cu ##um (Cu350@EEJA), stripping: 40 min / 40 C / DMSO+TMAH stripper

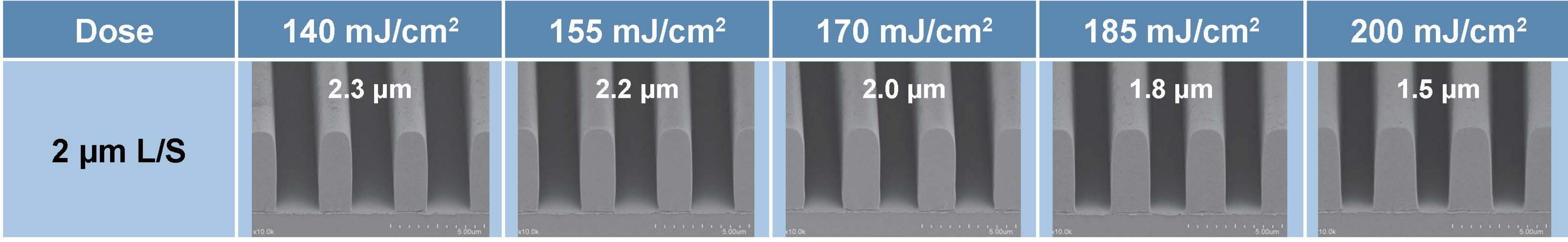
for Fine Pitch RDL

◆ Resolutions



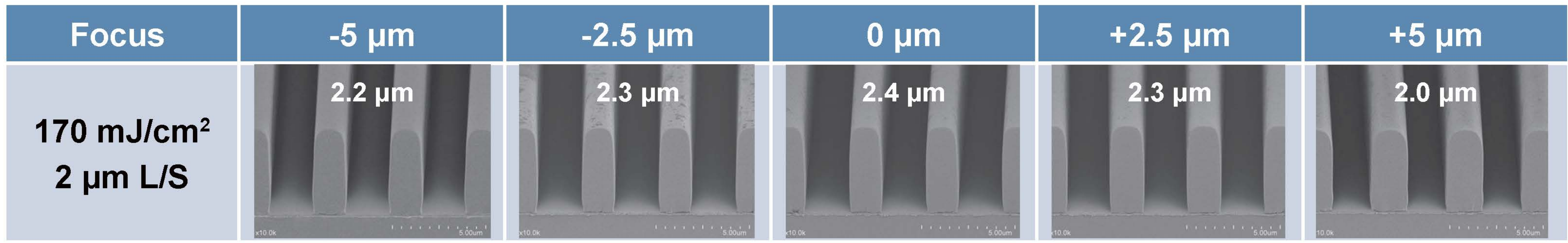
L/S	2.0 µm	1.8 µm	1.6 µm	1.4 µm	1.2 µm
170 mJ/cm^2	2.4 µm	2.2 µm	1.8 µm	1.4 µm	

◆ Dose margin



Dose	140 mJ/cm^2	155 mJ/cm^2	170 mJ/cm^2	185 mJ/cm^2	200 mJ/cm^2
2 µm L/S	2.3 µm	2.2 µm	2.0 µm	1.8 µm	1.5 µm

◆ DOF margin



Focus	-5 µm	-2.5 µm	0 µm	+2.5 µm	+5 µm
170 mJ/cm^2 2 µm L/S	2.2 µm	2.3 µm	2.4 µm	2.3 µm	2.0 µm

< Standard Patterning Conditions>

Substrate: Cu sputter wafer, Film Thickness after Dev.: 5 µm, Soft-bake : 110 C / 3 min,
Exposure: ### mJ/cm^2 (Canon FPA-5520 iV(i-line), NA=0.18, Focus= # µm inside from film surface),
Development : 60 sec x 2 times / 2.38 wt%TMAH